

NTS230N06E



N-Channel Enhancement Mode Trench Power MOSFET

Voltage: 60 Volts

Current: 25 Ampers

Package: TO-251

Features

- NH'S Advanced Trench Technology
- Low Rds(on) For Low On-State Loss
- High EAS For High Reliability
- Excellent Qg*Rds(on) Product(FOM)

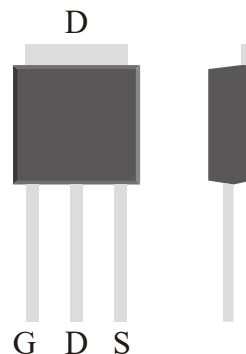
Typical Applications

- DC-DC Converter
- Battery Management System(BMS)
- Printed Circuit Board For Control Circuit
- Uninterruptible Power Supplies(UPS)

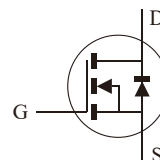
Product Summary

VDS Min.@Tj	60	V
Id Min.@Ta	25	A
RDS(ON)(TYP)@10V	23	mΩ

Diagram:



Polarity:



***100% UIS TESTED**

***100% ΔVDS TESTED**

Absolute Maximum Ratings (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 1)	Ta= 25 ℃	I _D	25	A
	Ta= 100 ℃		16	
Drain Current-Pulse (Note 1)	Tj< 150 ℃	I _{DM}	100	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25℃	Ta= 25 ℃	P _D	31	W
	Ta= 100 ℃		13	
Derating Factor		D _F	0.25	W/℃
Avalanche Current,Single Pulse (Note 1)	L= 0.5 mH	I _{AS}	16.5	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.16	L= 0.5 mH IAS= 16.5 A,RG= 10.0 Ω Starting Tj=25 ℃,VG= 10.0 V	E _{AS}	68	mJ

Thermal Characteristics (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 150	℃
Storage Temperature Range		T _{STD}	-55 to 150	℃
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25℃	R _{θJA}	100.0	℃/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 75mm x 45mm x 2.5mm Alu. Heat.	R _{θJC}	4.0	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig. 13).

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	BV _{DSS}	60	--	--	V
Bvdss Temperature Coefficient	ID=250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.07	--	V/℃
Drain-Source Leakage Current	VDS= 60 V,VGS=0V	I _{DSS}	--	--	1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= 12.5 A,VDS= 5 V	g _{fs}	--	38.0	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=250uA	V _{GS(TH)}	1.2	1.8	2.5	V
Drain-Source On Resistance	ID= 12.5 A,VGS= 10.0 V	R _{DS(ON)}	--	23.0	30.0	mΩ
	ID= 12.5 A,VGS= 4.5 V		--	29.9	45.0	
Dynamic Characteristics						
Input Capacitance	VDS= 30 V	C _{iss}	--	1025.0	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	65.0	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	46.0	--	pF
Switching Paramters (Test Circuit & Waveform See Fig.14)						
Turn-On Delay Time	VDS= 30 V	t _{d(on)}	--	2.8	--	ns
Turn-On Rise Time	VGS= 10.0 V	t _r	--	16.5	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	21.0	--	ns
Turn-Off Rise Time		t _f	--	5.5	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.15)						
Total Gate Charge	VDS= 30 V	Q _g	--	47.0	--	nC
Gate-Source Charge	VGS= 10.0 V	Q _{gs}	--	6.0	--	nC
Gate-Drain Charge	ID= 12.5 A	Q _{gd}	--	14.0	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.17)						
Max. Diode Forward Cuurent		I _S	--	--	25	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	100	A
Diode Forward Voltage	ID= 12.5 A,VGS=0V	V _{SD}	--	0.85	1.5	V
Reverse Recovery Time	IS= 12.5 A,di/dt= 100 A/us	t _{rr}	--	12.0	--	ns
Reverse Recovery Charge	VGS= 0.0 V	Q _{rr}	--	7.0	--	nC
Reverse Recovery Current		I _{RRM}	--	1.2	--	A

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Typical Characteristics Curves

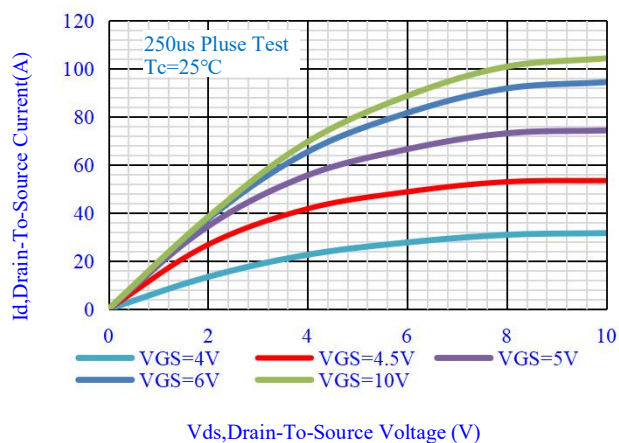


Fig.1-Output Characteristics

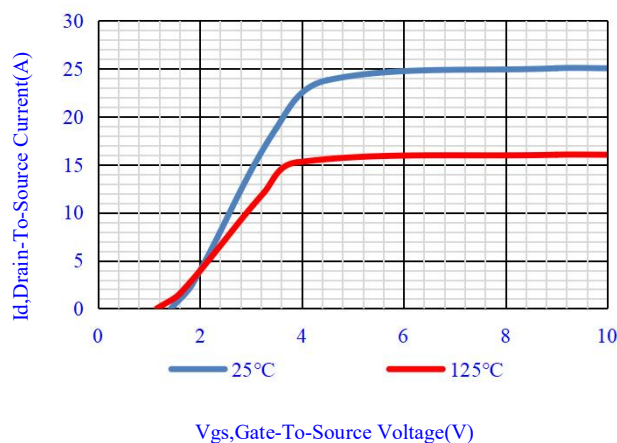


Fig.2-Transfer Characteristics

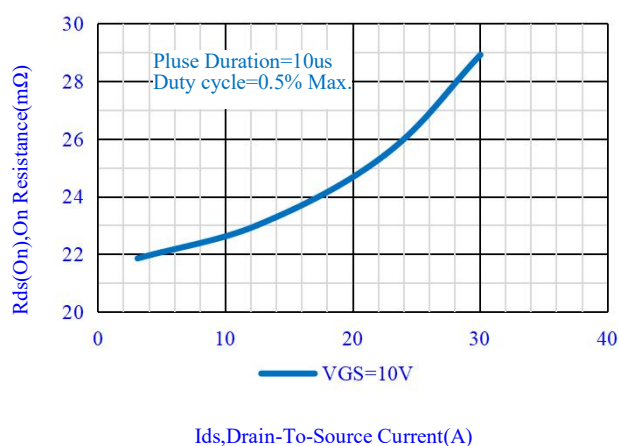


Fig.3-On Resistance Vs. Drain Current

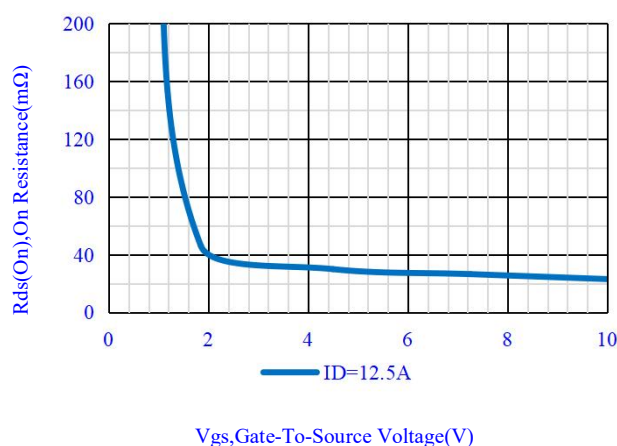


Fig.4-On Resistance Vs. Gate Source Voltage

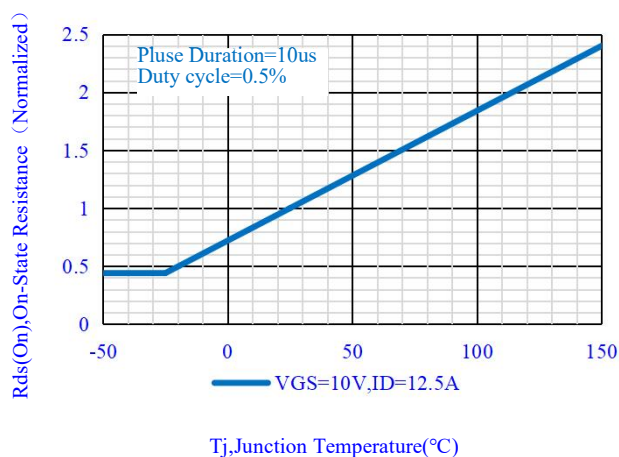


Fig.5-On Resistance Vs. Junction Temperature

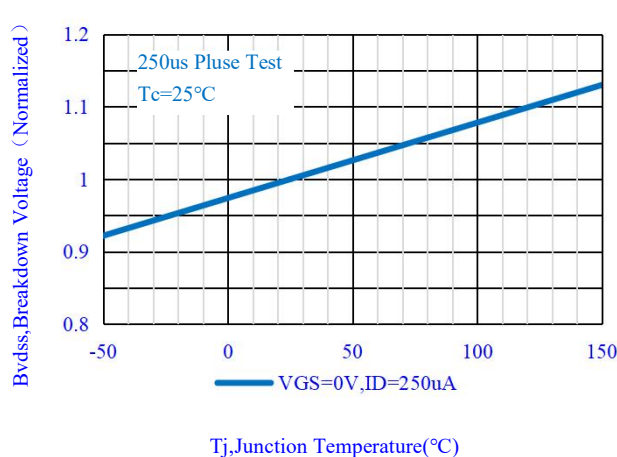


Fig.6-Breakdown Voltage Vs. Junction Temperature

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Typical Characteristics Curves

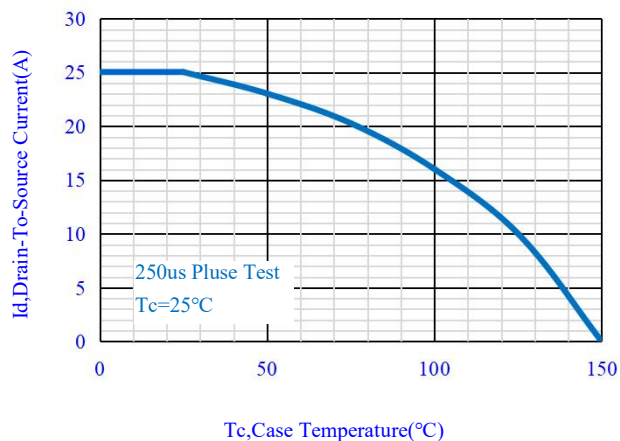


Fig.7-Maximum Continuous Drain Current Vs. Case Temperature

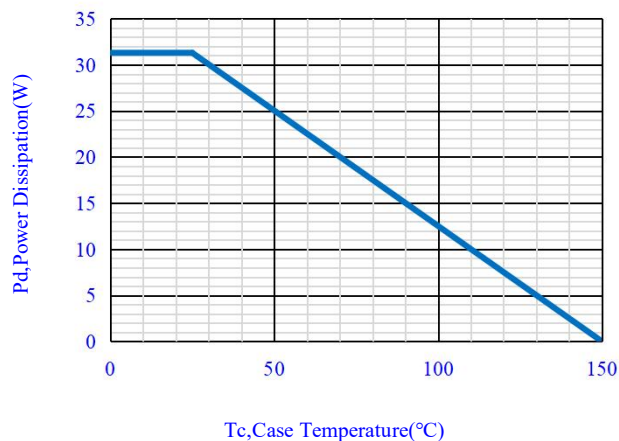


Fig.8-Maximum Power Dissipation Vs. Case Temperature

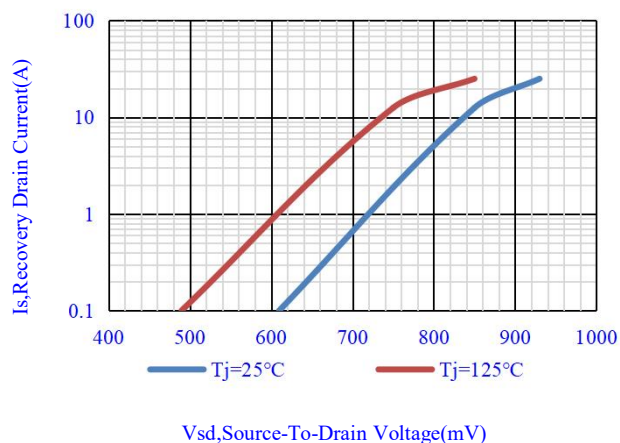


Fig.9-Source-To-Drain Diode Forward Voltage

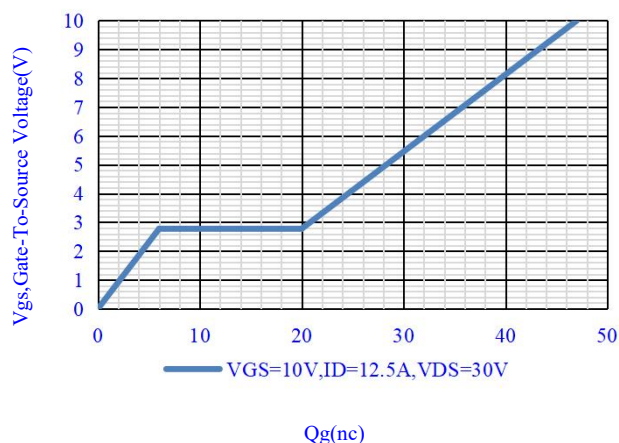


Fig.10-Gate Charge Waveform

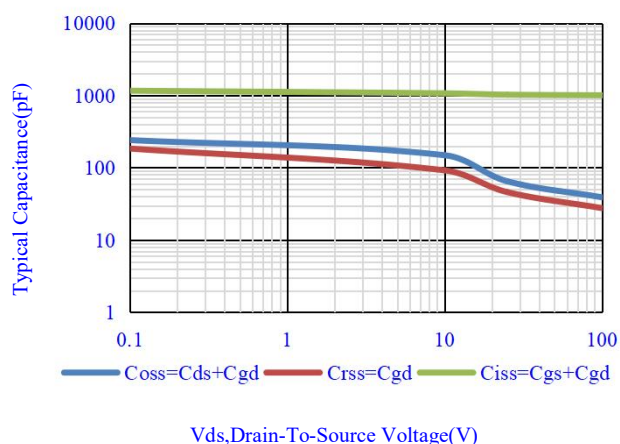


Fig.11-Typical Capacitance Vs. Drain-To-Source Voltage

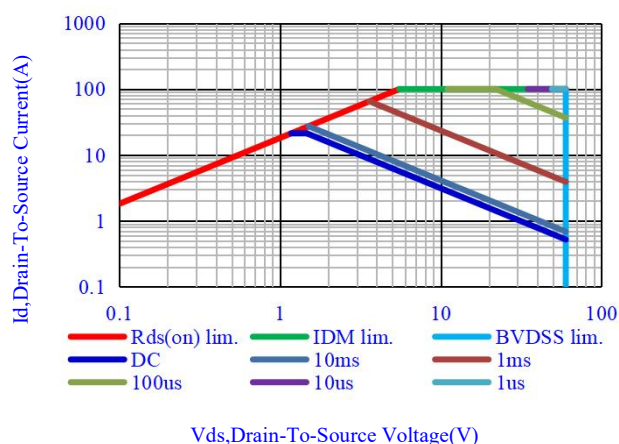


Fig.12-Maximum Safe Operating Area(SOA)

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Typical Characteristics Curves

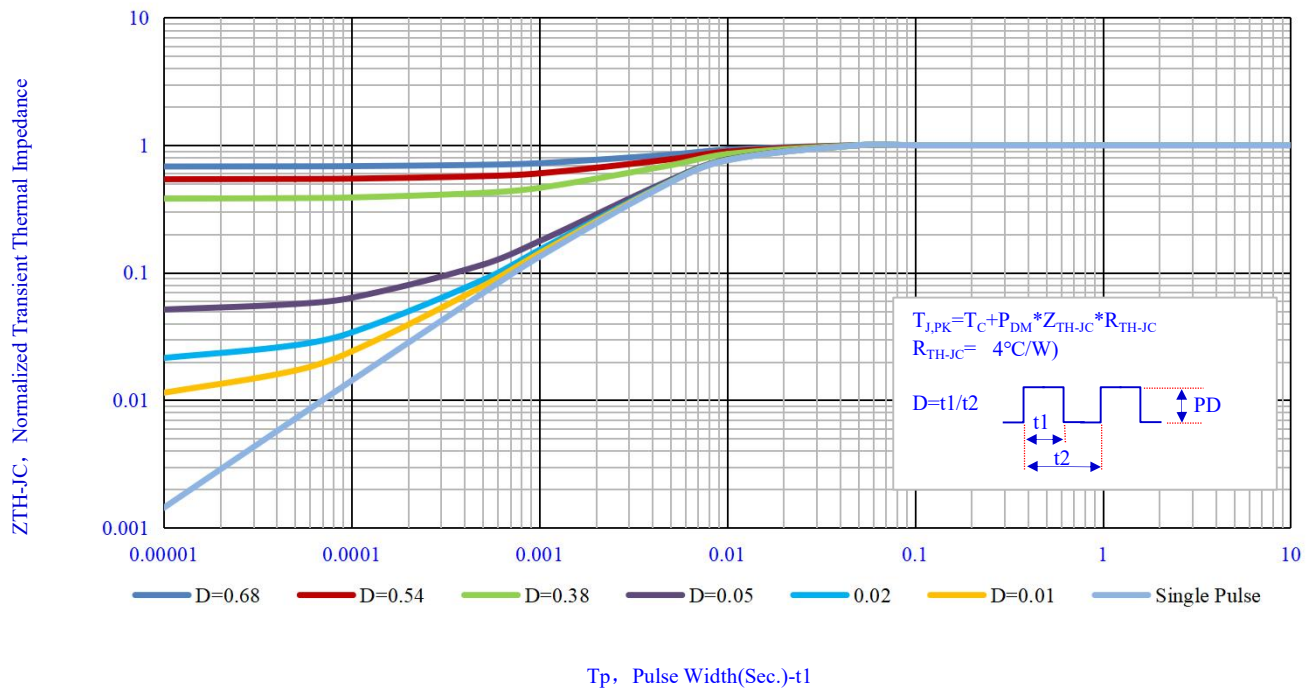


Fig.13- Normalized Maximum Transient Thermal Impedance Vs.Pulse Width

Test Circuit & Waveform

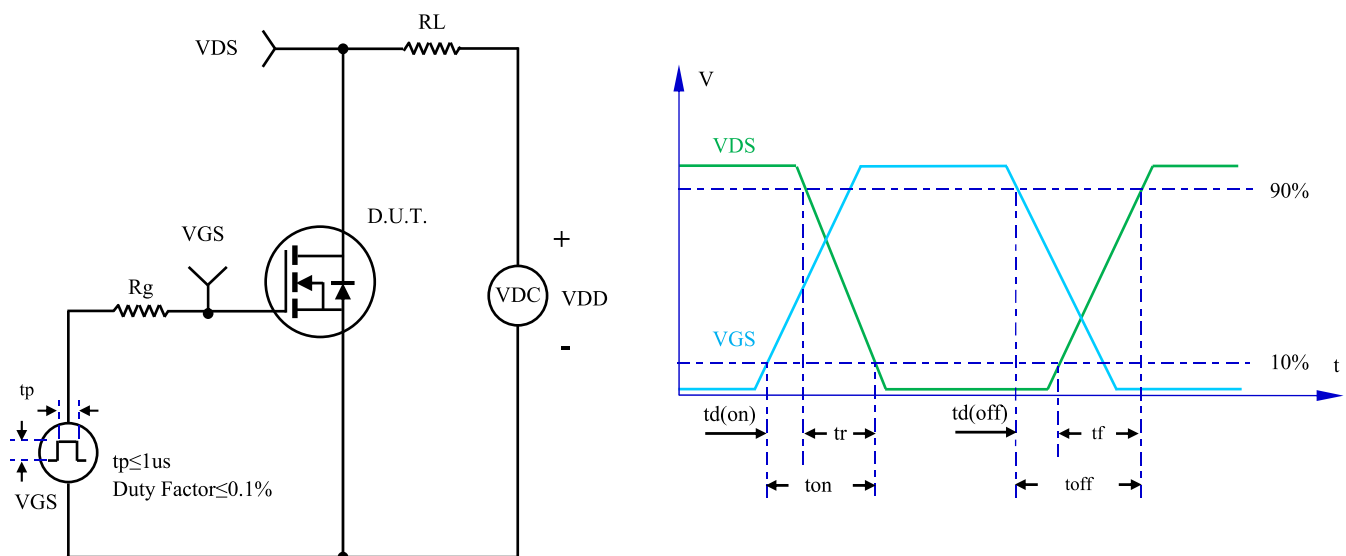


Fig.14- Resistive Switching Test Circuit & Waveform

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Test Circuit & Waveform

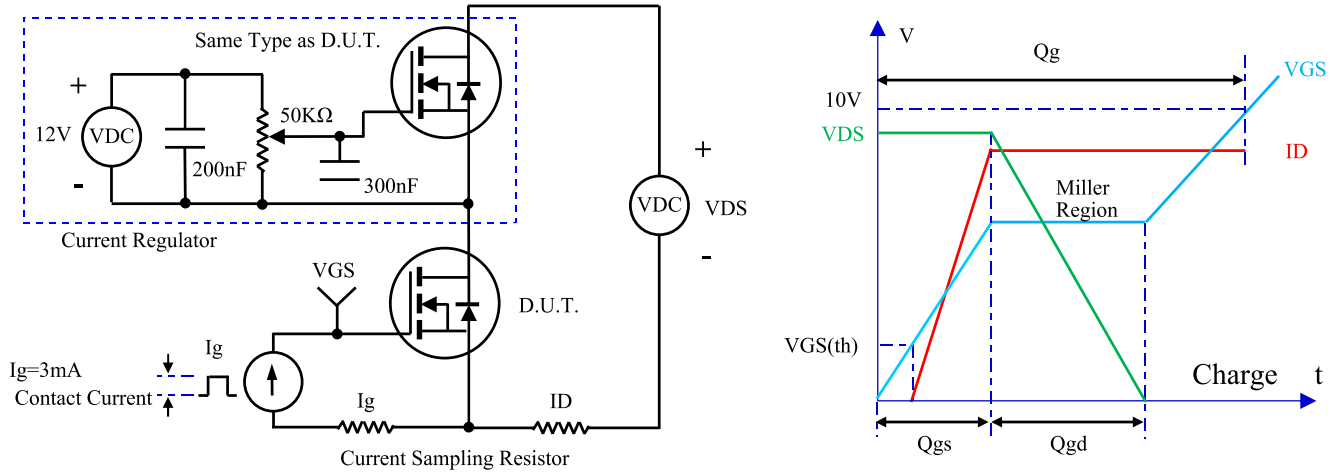


Fig.15- Gate Charge Test Circuit & Waveform

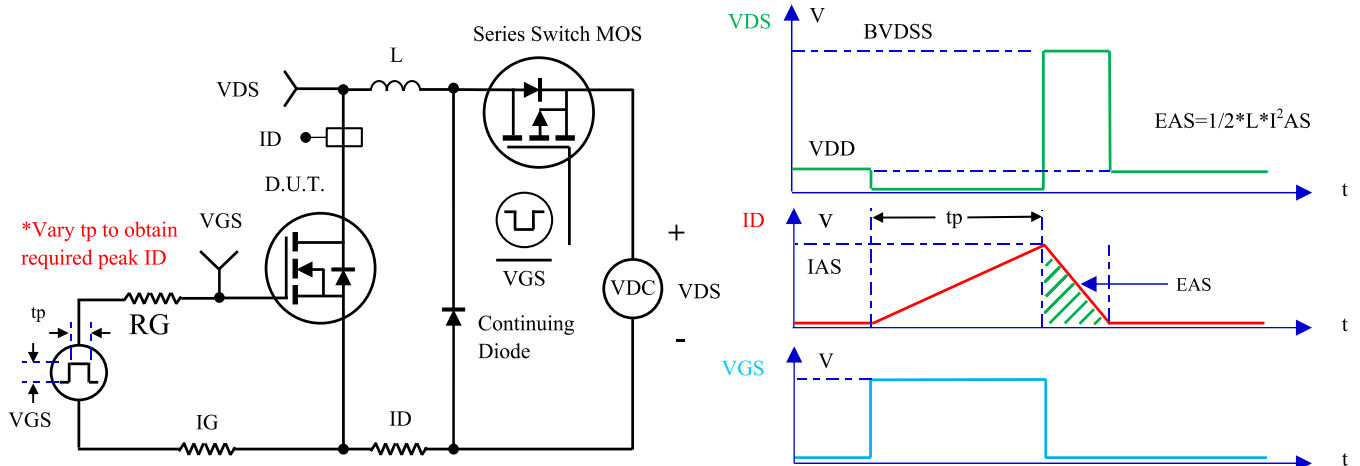


Fig.16- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

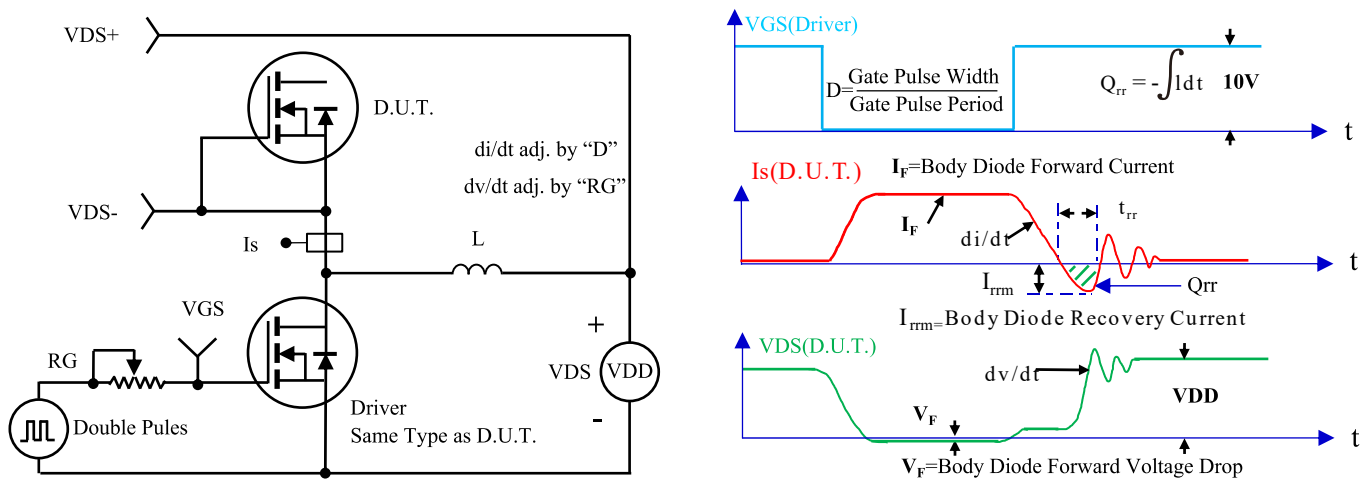


Fig.17- Diode Recovery Test Circuit & Waveform

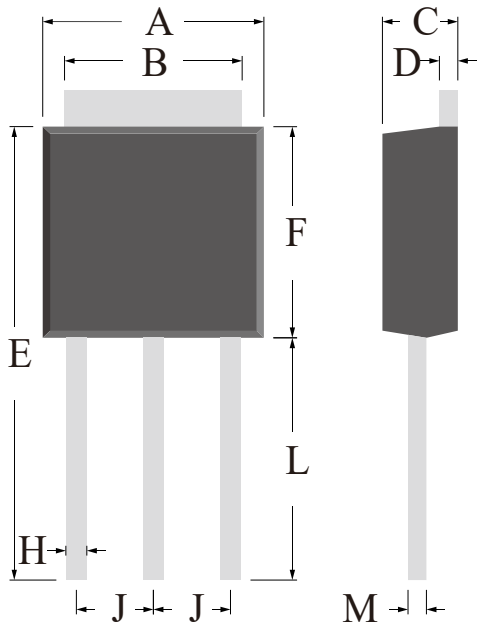
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OUTLINE DRAWINGS

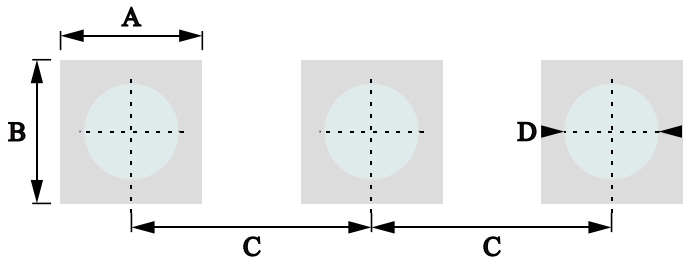
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OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.10	-	7.10	0.2402	-	0.2795
B	4.80	-	5.80	0.1890	-	0.2283
C	1.95	-	2.55	0.0768	-	0.1004
D	0.35	-	0.75	0.0138	-	0.0295
E	13.50	-	15.00	0.5315	-	0.5906
F	5.60	-	6.60	0.2205	-	0.2598
H	0.40	-	0.85	0.0157	-	0.0335
J	2.10	-	2.50	0.0827	-	0.0984
L	6.00	-	8.00	0.2362	-	0.3150
M	0.35	-	0.75	0.0138	-	0.0295

RECOMMEDND LAYOUT DRAWINGS

TO-251



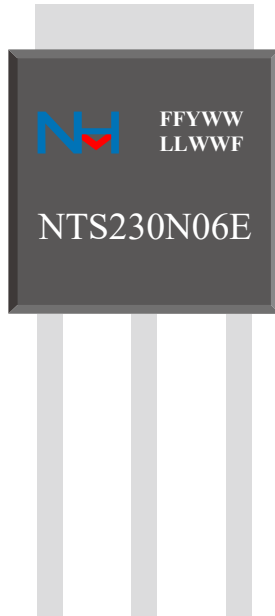
OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	1.60	-	-	0.0630	-
B	-	1.60	-	-	0.0630	-
C	-	2.30	-	-	0.0906	-
D	-	0.90	-	-	0.0354	-

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MARKING INFORMATION



MARKING INSTRUCTIONS

NH=Niuhan Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Inernal Code,According To Actual Changes
NTS230N06E=Model

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TO-251	P1	0.361	Tube	50	4000	20000

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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat -Temperature Min(T _S min) -Temperature Max(T _S max) -Time(t _s min to t _s max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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